### DISCRETE SEMICONDUCTORS

# DATA SHEET

### **BS250**

# P-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

**April 1995** 





### P-channel enhancement mode vertical D-MOS transistor

**BS250** 

#### **DESCRIPTION**

P-channel enhancement mode vertical D-MOS transistor in TO-92 variant envelope and intended for use in relay, high-speed and line-transformer drivers.

### **FEATURES**

- Low R<sub>DS(on)</sub>
- Direct interface to C-MOS
- High-speed switching
- No second breakdown

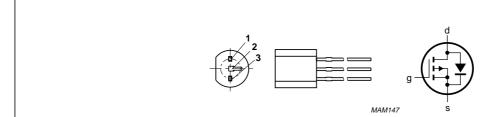
PINNING -	TO-92	VARIANT

- 1 = source
- 2 = gate
- 3 = drain

#### QUICK REFERENCE DATA

Drain-source voltage	$-V_{DS}$	max.	45 V	
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20 V	
Drain current (DC)	$-I_D$	max.	0.25 A	
Total power dissipation				
up to $T_{amb}$ = 25 °C	$P_{tot}$	max.	0.83 W	
Drain-source ON-resistance			•	
$-I_D = 200 \text{ mA}; -V_{GS} = 10 \text{ V}$	D	typ.	9 Ω	
-ib = 200 iiiA, -vgg = 10 v	$R_{DS(on)}$	max.	14 Ω	
Transfer admittance				
$-I_D = 200 \text{ mA}; -V_{DS} = 15 \text{ V}$	Y <sub>fs</sub>	typ.	125 mS	

#### **PIN CONFIGURATION**



Note: Various pinout configurations available.

Fig.1 Simplified outline and symbol.

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D-10103 (ransisto)					
RATINGS	Cystom (IEC 424)				
Limiting values in accordance with the Absolute Maximum				45	
Drain-source voltage	$-V_{DS}$		max.		V
Gate-source voltage (open drain)	± V <sub>GSO</sub>		max.		V
Drain current (DC)	-I <sub>D</sub>		max.	0.25	
Drain current (peak value)	-I <sub>DM</sub>		max.	0.5	
Total power dissipation up to T <sub>amb</sub> = 25 °C (note 1)	P <sub>tot</sub>		max.	0.83	
Storage temperature range	T <sub>stg</sub>		–65 to		
Junction temperature	$T_{j}$		max.	150	°C
THERMAL RESISTANCE					
From junction to ambient (note 1)	R <sub>th j-a</sub>		=	150	K/W
Note					
1. Transistor mounted on printed-circuit board, max. lead	l length 4 mm.				
CHARACTERISTICS					
$T_j$ = 25 °C unless otherwise specified					
Drain-source breakdown voltage					
$-I_D = 100 \mu\text{A};  V_{GS} = 0$	$-V_{(BR)DSS}$	min.	45		V
Drain-source leakage current					
$-V_{DS} = 25 \text{ V}; V_{GS} = 0$	-I <sub>DSS</sub>	max.	0.5		μΑ
Gate-source leakage current					
$-V_{GS} = 15 \text{ V}; V_{DS} = 0$	-I <sub>GSS</sub>	max.	20		nA
Gate threshold voltage					
$-I_D = 1 \text{ mA}; V_{DS} = V_{GS}$	$-V_{GS(th)}$	min.		1.0 3.5	
		max.		3.3	V
Drain-source ON-resistance					_
$-I_D = 200 \text{ mA}; -V_{GS} = 10 \text{ V}$	R <sub>DS(on)</sub>	typ.		9 14	Ω
		max.		14	52
Transfer admittance					
$-I_D = 200 \text{ mA}; -V_{DS} = 15 \text{ V}$	Y <sub>fs</sub>	typ.		125	mS
Input capacitance at f = 1 MHz				00	_
$-V_{DS} = 10 \text{ V}; V_{GS} = 0$	$C_{iss}$	typ. max.			pF pF
		max.		40	ы
Output capacitance at f = 1 MHz					_
$-V_{DS} = 10 \text{ V}; V_{GS} = 0$	C <sub>oss</sub>	typ.			pF pF
		max.		30	Ы
Feedback capacitance at f = 1 MHz				_	_
$-V_{DS} = 10 \text{ V}; V_{GS} = 0$	$C_{rss}$	typ.		5 10	pF pF
		max.		10	ρı

### P-channel enhancement mode vertical D-MOS transistor

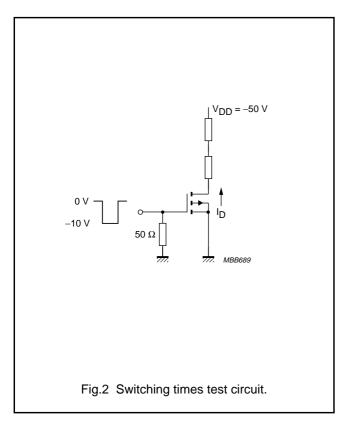
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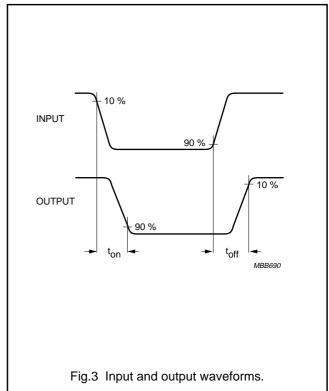
Switching times (see Figs 2 and 3)

$$-I_D = 200 \text{ mA}; -V_{DD} = 40 \text{ V}; -V_{GS} = 0 \text{ to } 10 \text{ V}$$

 $t_{on}$ 

typ. typ. 4 ns 10 ns





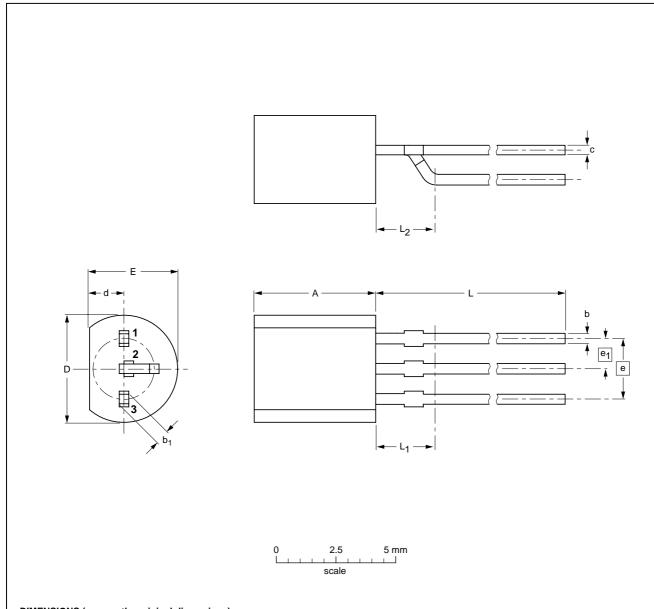
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### **PACKAGE OUTLINES**

### Plastic single-ended leaded (through hole) package; 3 leads (on-circle)

**SOT54** variant



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max	L <sub>2</sub> max
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	2.5

### Notes

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT54 variant		TO-92	SC-43			97-04-14

### P-channel enhancement mode vertical D-MOS transistor

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#### **DEFINITIONS**

Data sheet status			
Objective specification	This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Application information			
Where application information is given, it is advisory and does not form part of the specification.			

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## P-channel enhancement mode vertical D-MOS transistor

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